2SC2631

Silicon NPN epitaxial planar type

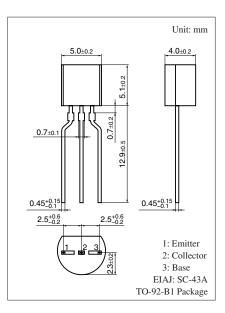
For low-frequency high breakdown voltage amplification Complementary to 2SA1123

Features

- \bullet Satisfactory linearity of forward current transfer ratio h_{FE}
- High collector-emitter voltage (Base open) V_{CEO}
- \bullet Small collector output capacitance (Common base, input open circuited) C_{ob}

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	150	V
Collector-emitter voltage (Base open)	V _{CEO}	150	V
Emitter-base voltage (Collector open)	V _{EBO}	5	V
Collector current	I _C	50	mA
Peak collector current	I _{CP}	100	mA
Collector power dissipation	P _C	750	mW
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 100 \ \mu A, \ I_{\rm B} = 0$	150			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = 10 \ \mu A, \ I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 100 \text{ V}, I_E = 0$			1	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = 5 V, I_C = 10 mA$	130		330	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 3 \text{ mA}$			1	V
Transition frequency	f _T	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$		160		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			3	pF
(Common base, input open circuited)						
Noise voltage	NV	$V_{CE} = 10 \text{ V}, I_C = 1 \text{ mA}, G_V = 80 \text{ dB}$		150	300	mV
		$R_g = 100 \text{ k}\Omega$, Function = FLAT				

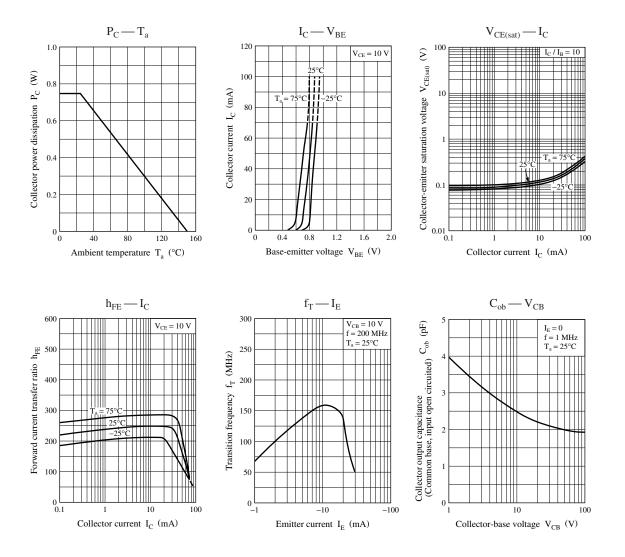
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification

S

Rank	R				

		-
$h_{\rm FE}$	130 to 220	185 to 330

Panasonic



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